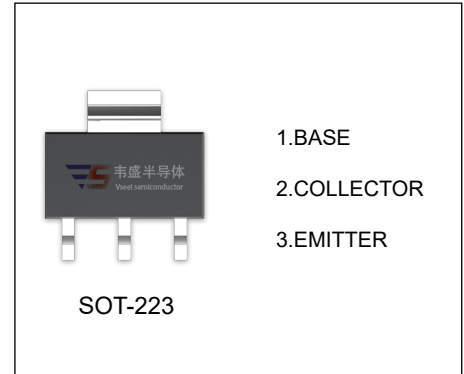


PZTA64 TRANSISTOR (PNP)

FEATURES

- Low Voltage and High Current
- High Current Gain Applications



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-10	V
I_C	Collector Current	-500	mA
P_C	Collector Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	125	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$I_C=-0.1\text{mA}, I_B=0$	-30			V
Collector cut-off current	I_{CBO}	$V_{CB}=-30\text{V}, I_E=0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-10\text{V}, I_C=0$			-100	nA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$	10000			
	$h_{FE(2)}^*$	$V_{CE}=-5\text{V}, I_C=-100\text{mA}$	20000			
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=-100\text{mA}, I_B=-0.1\text{mA}$			-1.5	V
Base-emitter voltage	V_{BE}^*	$V_{CE}=-5\text{V}, I_C=-100\text{mA}$			-2	V
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$	125			MHz

*Pulse test: pulse width $\leq 350\mu\text{s}$, duty cycle $\leq 2.0\%$.